
2SK1153, 2SK1154

Silicon N-Channel MOS FET

HITACHI

ADE-208-1246 (Z)
1st. Edition
Mar. 2001

Application

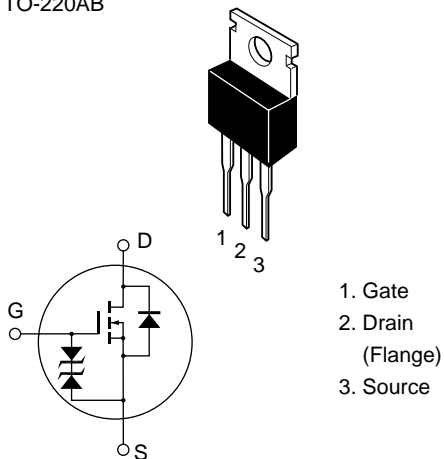
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-220AB



2SK1153, 2SK1154

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1153	V_{DSS}	450	V
	2SK1154		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	3	A
Drain peak current		$I_{D(pulse)}^{*1}$	12	A
Body to drain diode reverse drain current		I_{DR}	3	A
Channel dissipation		Pch^{*2}	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. PW 10 μ s, duty cycle 1%

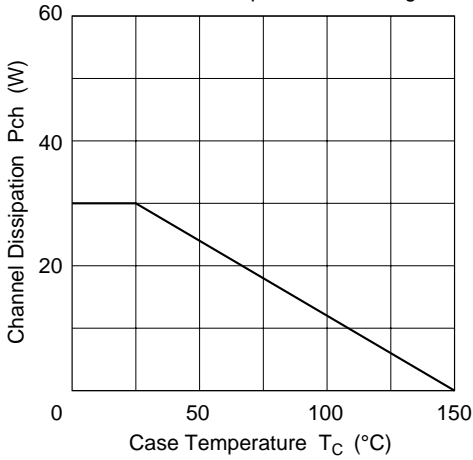
2. Value at T_c = 25°C

Electrical Characteristics (Ta = 25°C)

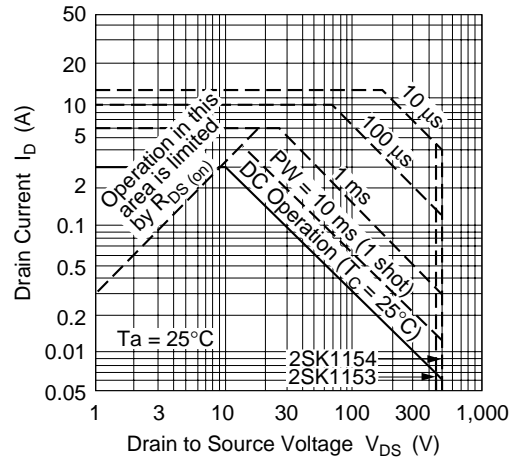
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1153 $V_{(BR)DSS}$	450	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
	2SK1154	500				
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK1153 I_{DSS}	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
	2SK1154					$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on statesresistance	2SK1153 $R_{DS(on)}$	—	2.0	2.8		$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
	2SK1154	—	2.2	3.0		
Forward transfer admittance	yfs	1.5	2.5	—	S	$I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	—	330	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	—	90	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	Crss	—	15	—	pF	
Turn-on delay time	$t_{d(on)}$	—	7	—	ns	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	20	—	ns	$R_L = 15$
Turn-off delay time	$t_{d(off)}$	—	30	—	ns	
Fall time	t_f	—	20	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 3 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	300	—	ns	$I_F = 3 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

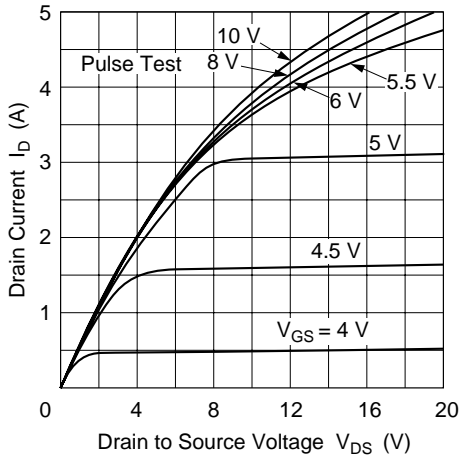
Power vs. Temperature Derating



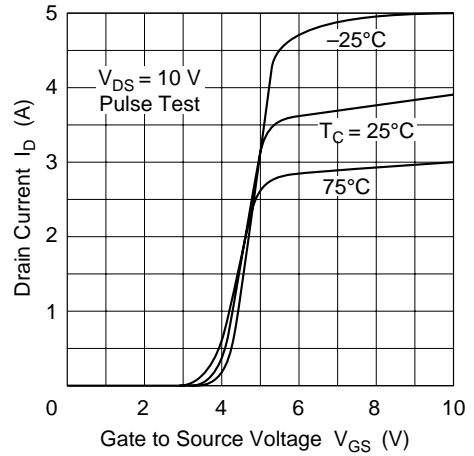
Maximum Safe Operation Area



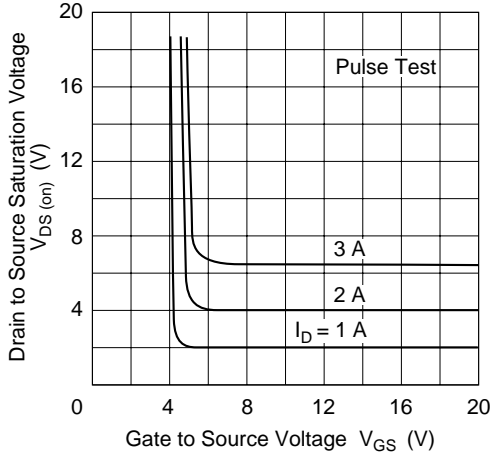
Typical Output Characteristics



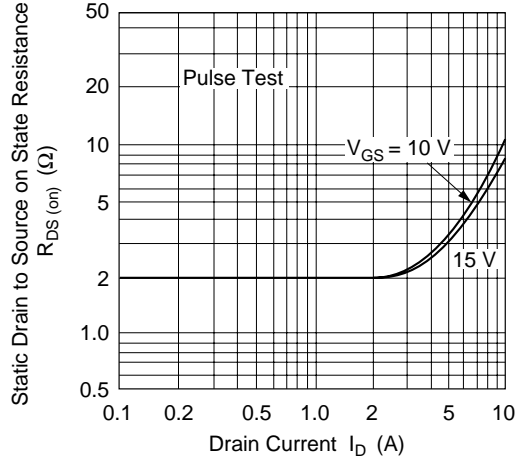
Typical Transfer Characteristics



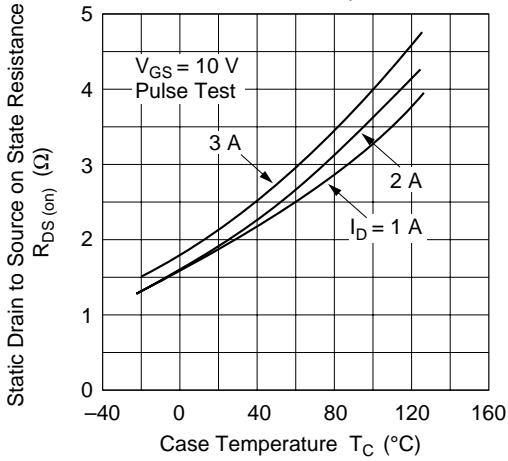
Drain to Source Saturation Voltage vs. Gate to Source Voltage



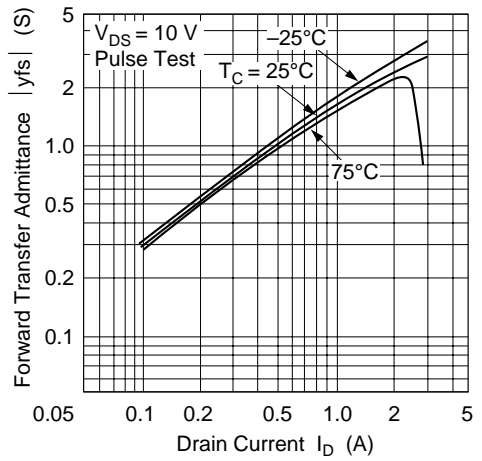
Static Drain to Source on State Resistance vs. Drain Current



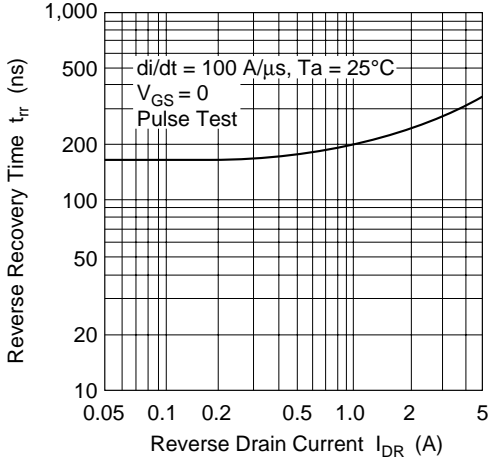
Static Drain to Source on State Resistance vs. Temperature



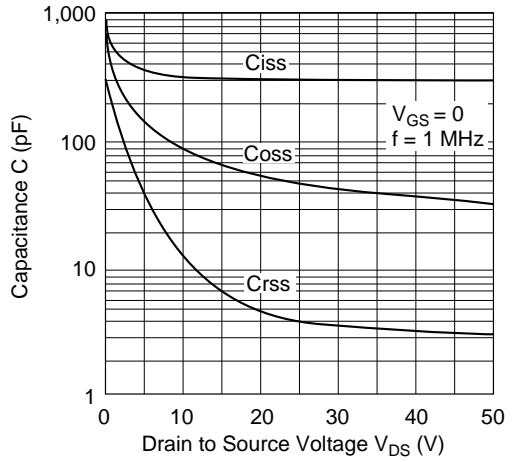
Forward Transfer Admittance vs. Drain Current



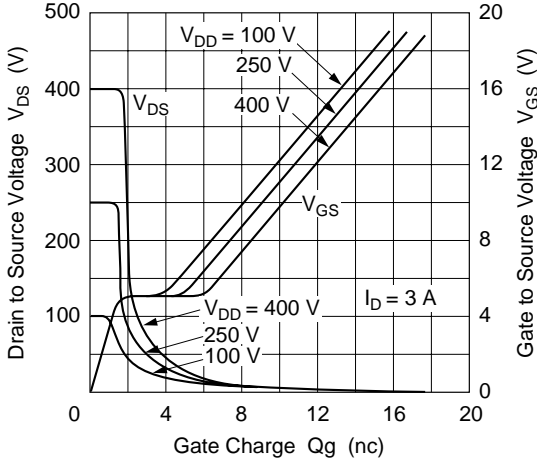
Body to Drain Diode Reverse Recovery Time



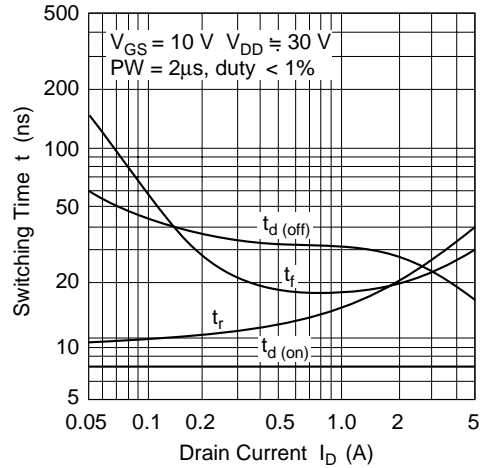
Typical Capacitance vs. Drain to Source Voltage

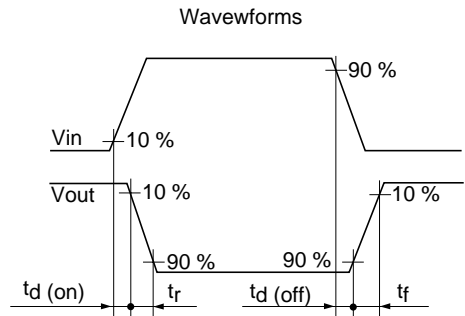
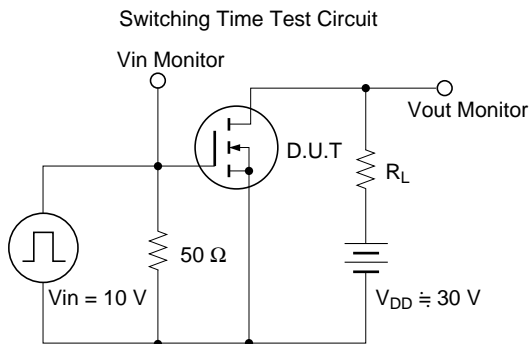
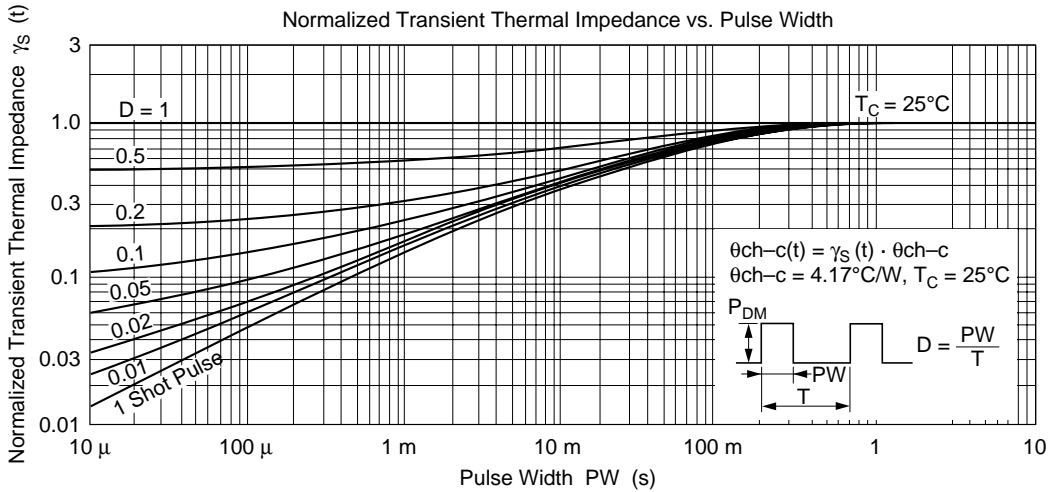
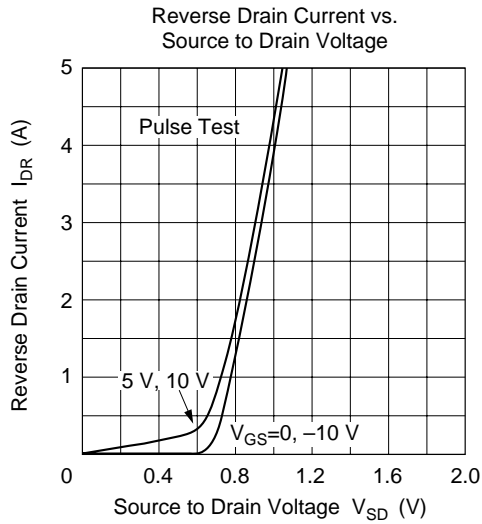


Dynamic Input Characteristics



Switching Characteristics

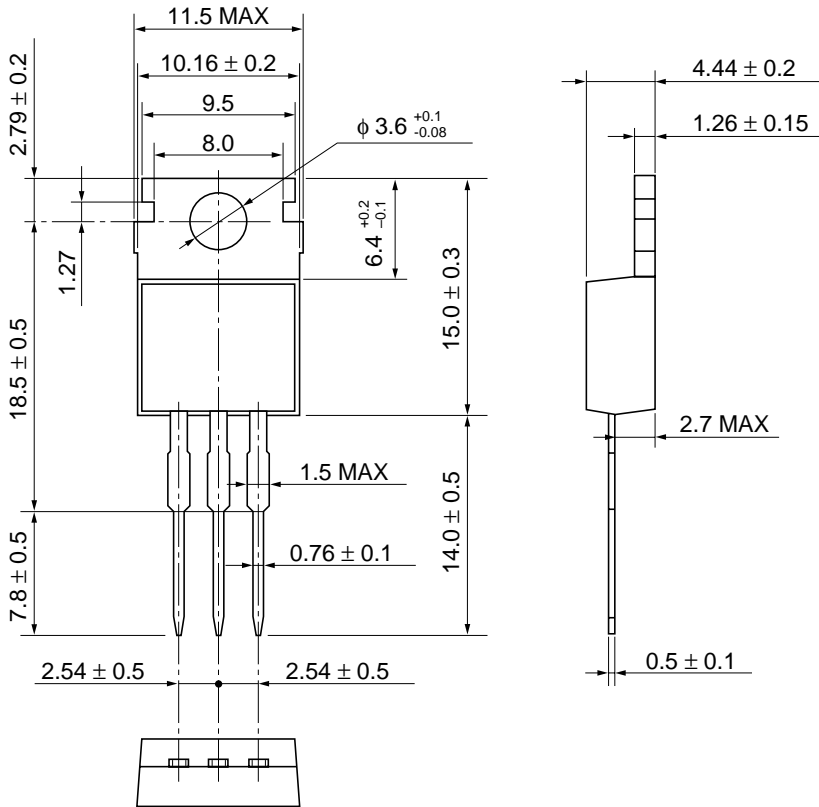




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

Cautions

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